## Claim Amendments

Please amend claims 1, 9, and 17 as follows:

## Listing of Claims

1. (currently amended) A method of forming an MIM capacitor to prevent plasma induced damage to a capacitor dielectric, comprising:

providing a substrate;

providing a capacitor opening in said substrate;

providing a bottom electrode in said capacitor opening; thermally annealing said bottom electrode;

providing a <u>capacitor</u> dielectric layer <u>in said</u>

<u>capacitor opening</u> on said bottom electrode; and

depositing a top electrode on said <u>capacitor</u> dielectric layer using a plasma-free deposition process.

2. (original) The method of claim 1 wherein said top electrode has a substantially organic-free content.

- 3. (original) The method of claim 1 wherein said annealing said bottom electrode comprises exposing said bottom electrode to nitrogen gas while subjecting said bottom electrode to thermal processing.
- 4. (original) The method of claim 3 wherein said top electrode has a substantially organic-free content.
- 5. (original) The method of claim 1 wherein said top electrode is deposited on said dielectric layer using a deposition temperature of no greater than about 400 degrees C.
- 6. (original) The method of claim 5 wherein said top electrode has a substantially organic-free content.
- 7. (original) The method of claim 5 wherein said annealing said bottom electrode comprises exposing said bottom electrode to nitrogen gas while subjecting said bottom electrode to thermal processing.
- 8. (original) The method of claim 7 wherein said top electrode has a substantially organic-free content.

9. (currently amended) A method of forming an MIM capacitor to prevent plasma induced damage to a high-K capacitor dielectric, comprising:

providing a substrate;

providing a capacitor opening in said substrate;

providing a bottom electrode in said capacitor opening;

thermally annealing said bottom electrode;

depositing a top electrode on said  $\frac{\text{high-K}}{\text{dielectric}}$  layer using a plasma-free deposition process.

10. (original) The method of claim 9 wherein said top electrode has a substantially organic-free content.

- 11. (original) The method of claim 9 wherein said annealing said bottom electrode comprises exposing said bottom electrode to nitrogen gas while subjecting said bottom electrode to thermal processing.
- 12. (original) The method of claim 9 wherein said top electrode is deposited on said dielectric layer using a deposition temperature of no greater than about 400 degrees C.
- 13. (original) The method of claim 9 wherein said plasma-free deposition process is a thermal chemical vapor deposition process or an atomic layer deposition process.
- 14. (original) The method of claim 13 wherein said top electrode has a substantially organic-free content.
- 15. (original) The method of claim 13 wherein said annealing said bottom electrode comprises exposing said bottom electrode to nitrogen gas while subjecting said bottom electrode to thermal processing.
- 16. (original) The method of claim 13 wherein said top electrode

is deposited on said dielectric layer using a deposition temperature of no greater than about 400 degrees C.

17. (currently amended) A method of forming an MIM capacitor to prevent plasma induced damage to a high-K capacitor dielectric, comprising:

providing a substrate;

providing a capacitor opening in said substrate;

providing a bottom electrode in said capacitor opening;

subjecting said bottom electrode to chemical mechanical planarization;

thermally annealing said bottom electrode;

providing a <a href="https://property.com/high-K">high-K</a> dielectric layer in said capacitor opening on said bottom electrode; and

depositing a top electrode comprising TiN on said high-

 $\underline{K}$  dielectric layer using a plasma-free deposition process.

- 18. (original) The method of claim 17 wherein said top electrode has a substantially organic-free content.
- 19. (original) The method of claim 18 wherein said annealing said bottom electrode comprises exposing said bottom electrode to nitrogen gas while subjecting said bottom electrode to thermal processing.
- 20. (original) The method of claim 19 wherein said top electrode is deposited on said dielectric layer using a deposition temperature of no greater than about 400 degrees C.